

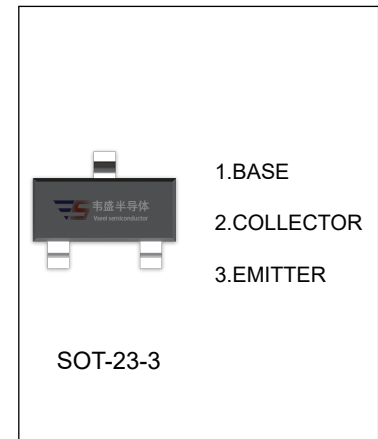
2SC1654 TRANSISTOR (NPN)

FEATURES

- High Frequency Power Amplifier Application
- Power Switching Applications

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	50	mA
P_C	Collector Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	833	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=130\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=3\text{V}, I_C=15\text{mA}$	90		400	
	$h_{FE(2)}$	$V_{CE}=3\text{V}, I_C=1\text{mA}$	70			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		2.3		pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	N5	N6	N7
RANGE	90 - 180	135 - 270	200 - 400
MARKING	N5	N6	N7

Static Characteristic

